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# May 2009

### **FDMS8674**

# N-Channel PowerTrench<sup>®</sup> MOSFET 30V, 21A, 5.0m $\Omega$

### **Features**

- Max  $r_{DS(on)}$  = 5.0m $\Omega$  at  $V_{GS}$  = 10V,  $I_D$  = 17A
- Max  $r_{DS(on)}$  = 8.0m $\Omega$  at  $V_{GS}$  = 4.5V,  $I_D$  = 14A
- Advanced Package and Silicon combination for low r<sub>DS(on)</sub> and high efficiency
- MSL1 robust package design
- RoHS Compliant

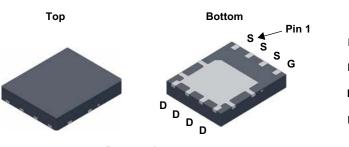


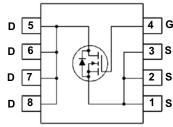
### **General Description**

The FDMS8674 has been designed to minimize losses in power conversion application. Advancements in both silicon and package technologies have been combined to offer the lowest  $r_{\text{DS}(on)}$  while maintaining excellent switching performance.

### **Applications**

- Computing VR & IMVP Vcore
- Secondary Side Synchronous Rectifier
- POL DC/DC Converter
- Oring FET/ Load Switch





Power 56

### MOSFET Maximum Ratings T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter			Ratings	Units
V <sub>DS</sub>	Drain to Source Voltage			30	V
V <sub>GS</sub>	Gate to Source Voltage			±20	V
	Drain Current -Continuous (Package limited)	T <sub>C</sub> = 25°C		21	
	-Continuous (Silicon limited)	T <sub>C</sub> = 25°C		94	1 ,
I <sub>D</sub>	-Continuous	T <sub>A</sub> = 25°C	(Note 1a)	17	Α Α
	-Pulsed			150	1
E <sub>AS</sub>	Single Pulse Avalanche Energy		(Note 3)	181	mJ
В	Power Dissipation	T <sub>C</sub> = 25°C		78	w
P <sub>D</sub>	Power Dissipation	T <sub>A</sub> = 25°C	(Note 1a)	2.5	] vv
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature R	ange		-55 to +150	°C

### **Thermal Characteristics**

$R_{\theta JC}$	Thermal Resistance, Junction to Case		1.6	°C/W
R <sub>e.IA</sub>	Thermal Resistance, Junction to Ambient (N	lote 1a)	50	C/VV

### **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS8674	FDMS8674	Power 56	13"	12mm	3000units

### **Electrical Characteristics** $T_J = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	cteristics					
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250μA, referenced to 25°C		25		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V			1	μА
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$			±100	nA

### On Characteristics

V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$	1.0	1.8	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I <sub>D</sub> = 250μA, referenced to 25°C		-6		mV/°C
		V <sub>GS</sub> = 10V, I <sub>D</sub> = 17A		4.1	5.0	
r <sub>DS(on)</sub>	Static Drain to Source On Resistance	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 14A		5.8	8.0	mΩ
		V <sub>GS</sub> = 10V, I <sub>D</sub> = 17A, T <sub>J</sub> = 125°C		5.8	8.3	
9 <sub>FS</sub>	Forward Transconductance	$V_{DD} = 10V, I_D = 17A$		87		S

### **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V - 45V V - 0V	1745	2320	pF
C <sub>oss</sub>	Output Capacitance	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1MHz	860	1145	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 111112	130	195	pF
R <sub>a</sub>	Gate Resistance	f = 1MHz	0.9		Ω

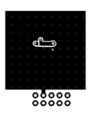
### **Switching Characteristics**

t <sub>d(on)</sub>	Turn-On Delay Time	., ,=,,,			11	20	ns
t <sub>r</sub>	Rise Time	V <sub>DD</sub> = 15V, I <sub>D</sub> = 1/A	$V_{DD} = 15V, I_{D} = 17A,$ $V_{GS} = 10V, R_{GEN} = 6\Omega$		4	10	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	V <sub>GS</sub> - 10V, K <sub>GEN</sub> -			26	42	ns
t <sub>f</sub>	Fall Time				3	10	ns
$Q_g$	Total Gate Charge	V <sub>GS</sub> = 0V to 10V			26	37	nC
Qg	Total Gate Charge	$V_{GS} = 0V \text{ to } 5V$	/ <sub>DD</sub> = 15V, I <sub>D</sub> = 17A		14	20	nC
Q <sub>gs</sub>	Gate to Source Charge	, ,	ID - 17A		4.8		nC
$Q_{gd}$	Gate to Drain "Miller" Charge				3.5		nC

### **Drain-Source Diode Characteristics**

V <sub>SD</sub> Source to Drain Diode Forward Voltage	V <sub>GS</sub> = 0V, I <sub>S</sub> = 2.1A (Note 2)	0.7	1.2	V	
V <sub>SD</sub>	Source to Drain Diode Forward voltage	V <sub>GS</sub> = 0V, I <sub>S</sub> = 17A	0.8	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> = 17A, di/dt = 100A/μs	40	64	ns
Q <sub>rr</sub>	Reverse Recovery Charge	- 17 A, αι/αι – 100 A/μs	30	48	nC

1.  $R_{\theta JA}$  is determined with the device mounted on a  $1\text{in}^2$  pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a. 50°C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper.

b. 125°C/W when mounted on a minimum pad of 2 oz copper.



<sup>2.</sup> Pulse Test: Pulse Width < 300 $\mu$ s, Duty cycle < 2.0%. 3. Starting T<sub>J</sub> = 25°C, L = 3mH, I<sub>AS</sub> = 11A, V<sub>DD</sub> = 30V, V<sub>GS</sub> = 10V.

### Typical Characteristics T<sub>J</sub> = 25°C unless otherwise noted

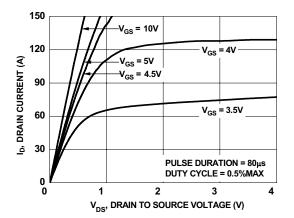


Figure 1. On-Region Characteristics

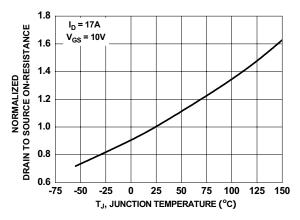


Figure 3. Normalized On-Resistance vs Junction Temperature

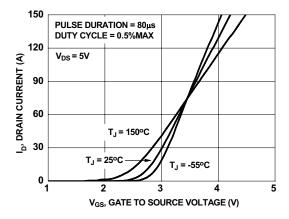


Figure 5. Transfer Characteristics

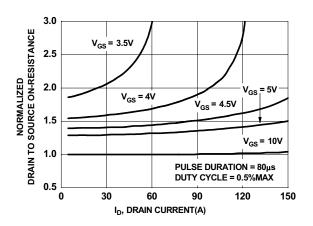


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

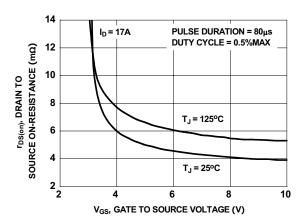


Figure 4. On-Resistance vs Gate to Source Voltage

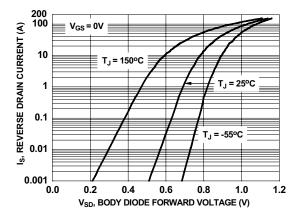


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

### Typical Characteristics $T_J = 25^{\circ}C$ unless otherwise noted

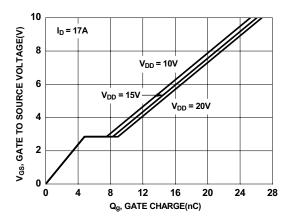


Figure 7. Gate Charge Characteristics

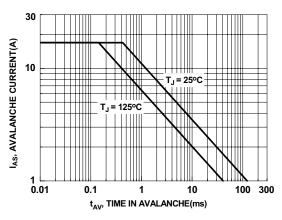


Figure 9. Unclamped Inductive Switching Capability

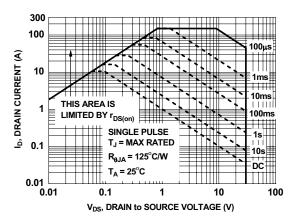


Figure 11. Forward Bias Safe Operating Area

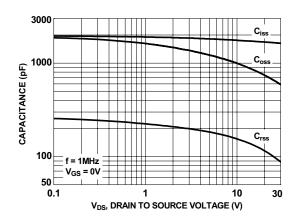


Figure 8. Capacitance vs Drain to Source Voltage

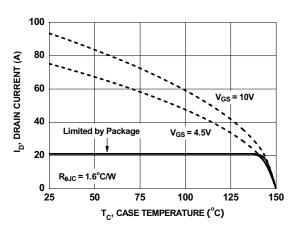


Figure 10. Maximum Continuous Drain Current vs Case Temperature

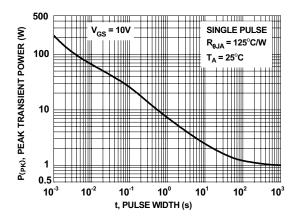


Figure 12. Single Pulse Maximum Power Dissipation

### Typical Characteristics T<sub>J</sub> = 25°C unless otherwise noted

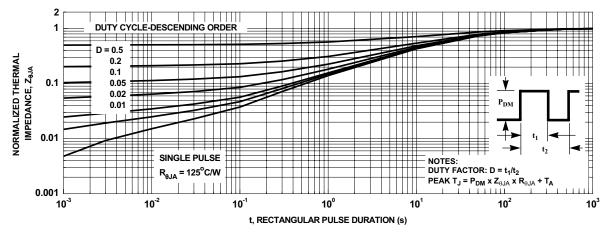
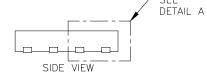
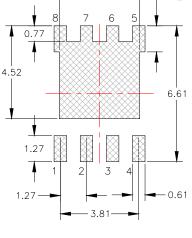


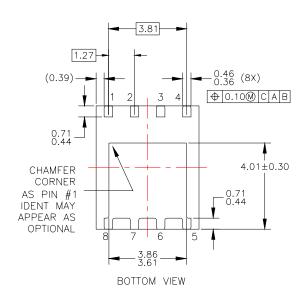
Figure 13. Transient Thermal Response Curve

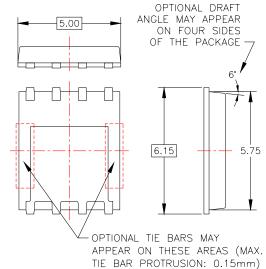
### **Dimensional Outline and Pad Layout** $\rightarrow$ A 5.00 PKG В 8 5 0.77 4.52 PKG & 6.00 6.61 1.27 PIN #1 4 IDENT MÄY TOP VIEW 2 3 4 APPEAR AS OPTIONAL -0.61 1.27 DETAIL A

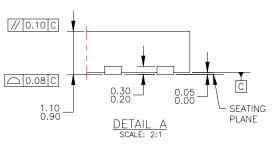




LAND PATTERN RECOMMENDATION







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- DATED OCTOBER 2002.

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  DIMENSIONS DO NOT INCLUDE BURRS
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  DIMENSIONING AND TOLERANCING PER
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